

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED MESA TYPE

# 2SD2550

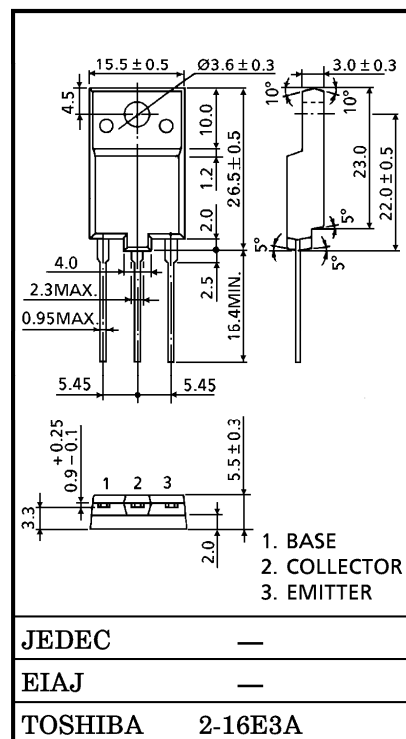
HORIZONTAL DEFLECTION OUTPUT FOR COLOR TV

Unit in mm

- High Voltage :  $V_{CB0} = 1700\text{ V}$
- Low Saturation Voltage :  $V_{CE(sat)} = 5.0\text{ V (Max)}$
- High Speed :  $t_f = 0.6\ \mu\text{s (Max)}$
- Built-in Damper Type
- Collector Metal (Fin) is Fully Covered with Mold Resin.

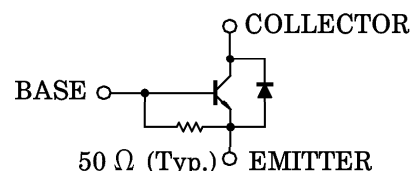
MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		$V_{CB0}$	1700	V
Collector-Emitter Voltage		$V_{CEO}$	600	V
Emitter-Base Voltage		$V_{EBO}$	5	V
Collector Current	DC	$I_C$	4	A
	Pulse	$I_{CP}$	8	
Base Current		$I_B$	2	A
Collector Power Dissipation ( $T_c = 25^\circ\text{C}$ )		$P_C$	50	W
Junction Temperature		$T_j$	150	$^\circ\text{C}$
Storage Temperature Range		$T_{stg}$	-55~150	$^\circ\text{C}$



Weight : 5.5 g (Typ.)

EQUIVALENT CIRCUIT



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## ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		$I_{CBO}$	$V_{CB} = 1700\text{ V}, I_E = 0$	—	—	1	mA
Emitter Cut-off Current		$I_{EBO}$	$V_{EB} = 5\text{ V}, I_C = 0$	66	—	200	mA
Emitter-Base Breakdown Voltage		$V_{(BR)EBO}$	$I_E = 400\text{ mA}, I_B = 0$	5	—	—	V
DC Current Gain		$h_{FE}$	$V_{CE} = 5\text{ V}, I_C = 1\text{ A}$	8	—	22	—
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C = 3\text{ A}, I_B = 0.8\text{ A}$	—	5	8	V
Base-Emitter Saturation Voltage		$V_{BE(sat)}$	$I_C = 3\text{ A}, I_B = 0.8\text{ A}$	—	—	1.2	V
Forward Voltage (Damper Diode)		$-V_F$	$I_F = 4\text{ A}$	—	1.5	2.0	V
Transition Frequency		$f_T$	$V_{CE} = 10\text{ V}, I_C = 0.1\text{ A}$	—	3	—	MHz
Collector Output Capacitance		$C_{ob}$	$V_{CE} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	85	—	pF
Switching Time	Storage Time	$T_{stg}$	$I_{CP} = 3\text{ A}, I_{B1}(\text{end}) = 0.8\text{ A}$ $f_H = 15.75\text{ kHz}$	—	7.5	10	$\mu\text{s}$
	Fall Time	$t_f$		—	0.3	0.6	

